

Saurav Roy

List of Publications by Year in descending order

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8
papers

290
citations

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252
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#	ARTICLE	IF	CITATIONS
1	In Situ Dielectric Al ₂ O ₃ /Î²-Ga ₂ O ₃ Interfaces Grown Using Metalâ€‘Organic Chemical Vapor Deposition. <i>Advanced Electronic Materials</i> , 2021, 7, 2100333.	5.1	17
2	High-k Oxide Field-Plated Vertical (001) Î²-Ga ₂ O ₃ Schottky Barrier Diode With Baligaâ€™s Figure of Merit Over 1 GW/cm ² . <i>IEEE Electron Device Letters</i> , 2021, 42, 1140-1143.	3.9	86
3	Multi-kV Class Î²-Ga ₂ O ₃ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm ² . <i>IEEE Electron Device Letters</i> , 2021, 42, 1272-1275.	3.9	50
4	Low temperature homoepitaxy of (010) Î²-Ga ₂ O ₃ by metalorganic vapor phase epitaxy: Expanding the growth window. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	56
5	Design of a Î²-Ga ₂ O ₃ Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4842-4848.	3.0	21
6	Delta-doped Î²-Ga ₂ O ₃ films with narrow FWHM grown by metalorganic vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	17
7	Schottky Barrier Height Engineering in Î²-Ga ₂ O ₃ Using SiO ₂ Interlayer Dielectric. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 286-294.	2.1	32
8	2-D Analytical Modeling of Surface Potential and Threshold Voltage for Vertical Super-Thin Body FET. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2106-2112.	3.0	11